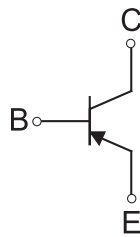


2SB776 TRANSISTOR (PNP)

FEATURES

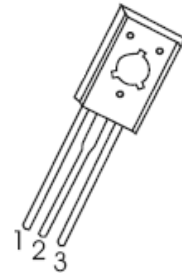
- High Current Output Up to 3A
- Low Saturation Voltage Power Dissipation

Equivalent Circuit



TO-126

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current –Continuous	-3	A
P _c	Collector Power Dissipation	1	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-5\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-20\text{mA}$	100			
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-200\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}, I_B=-200\text{mA}$			-2	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		45		pF

